74VHC595-Q100; 74VHCT595-Q100

8-bit serial-in/serial-out or parallel-out shift register with output latches

Rev. 1 — 15 November 2013

Product data sheet

1. General description

The 74VHC595-Q100; 74VHCT595-Q100 are high-speed Si-gate CMOS devices and are pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard No. 7A.

The 74VHC595-Q100; 74VHCT595-Q100 are 8-stage serial shift registers with a storage register and 3-state outputs. The shift registers have separate clocks.

Data is shifted on the positive-going transitions of the shift register clock input (SHCP). The data in each register is transferred to the storage register on a positive-going transition of the storage register clock input (STCP). If both clocks are connected together, the shift register is always one clock pulse ahead of the storage register.

The shift register has a serial input (DS) and a serial standard output (Q7S) for cascading. It is also provided with asynchronous reset (active LOW) for all 8 shift register stages. The storage register has 8 parallel 3-state bus driver outputs. Data in the storage register appears at the output whenever the output enable input (\overline{OE}) is LOW.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Balanced propagation delays
- All inputs have Schmitt-trigger action
- Inputs accept voltages higher than V_{CC}
- Input levels:
 - ◆ The 74VHC595-Q100 operates with CMOS input level
 - ◆ The 74VHCT595-Q100 operates with TTL input level
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V (C = 200 pf, R = 0 Ω)
- Multiple package options



3. Applications

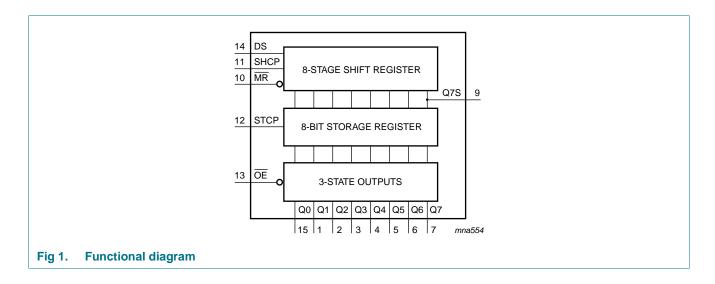
- Serial-to-parallel data conversion
- Remote control holding register

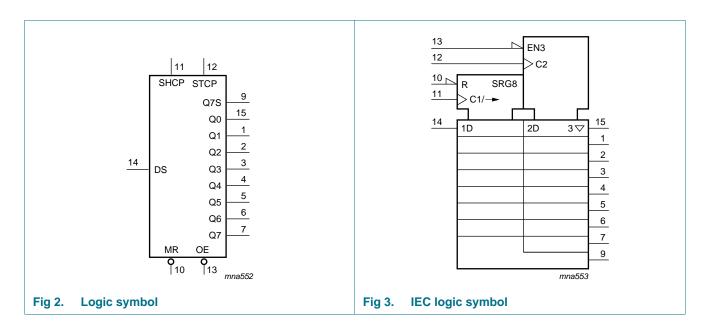
4. Ordering information

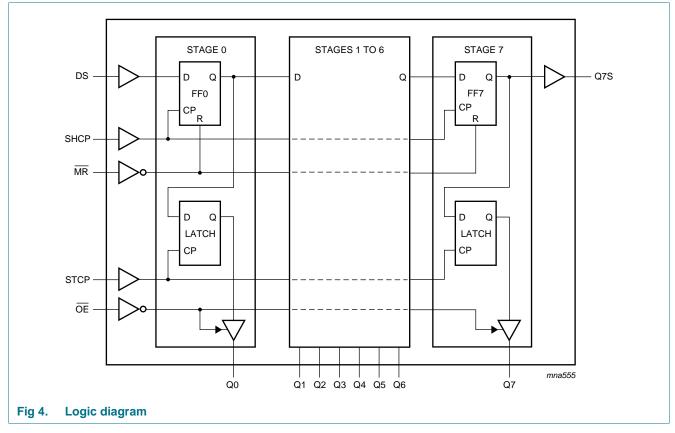
Table 1. Ordering information

Type number	Package											
	Temperature range	Name	Description	Version								
74VHC595D-Q100	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body	SOT109-1								
74VHCT595D-Q100			width 3.9 mm									
74VHC595PW-Q100	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16	SOT403-1								
74VHCT595PW-Q100			leads; body width 4.4 mm									
74VHC595BQ-Q100	–40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal	SOT763-1								
74VHCT595BQ-Q100			enhanced very thin quad flat package; no leads; 16 terminals; body $2.5 \times 3.5 \times 0.85$ mm									

5. Functional diagram

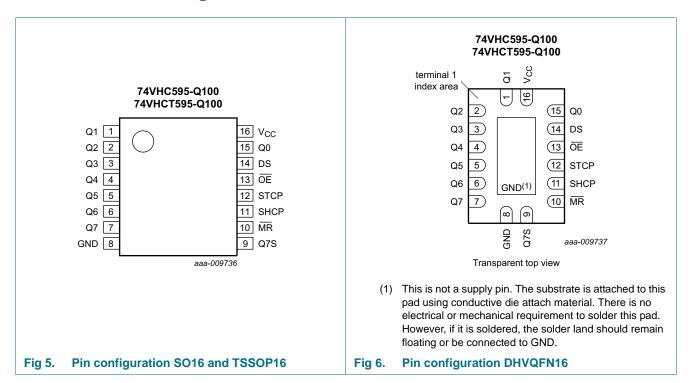






6. Pinning information

6.1 Pinning



6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
Q1	1	parallel data output 1
Q2	2	parallel data output 2
Q3	3	parallel data output 3
Q4	4	parallel data output 4
Q5	5	parallel data output 5
Q6	6	parallel data output 6
Q7	7	parallel data output 7
GND	8	ground (0 V)
Q7S	9	serial data output
MR	10	master reset (active LOW)
SHCP	11	shift register clock input
STCP	12	storage register clock input
ŌE	13	output enable input (active LOW)
DS	14	serial data input
Q0	15	parallel data output 0
V _{CC}	16	supply voltage

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7. Functional description

Table 3. Function table[1]

Contro	ol			Input	Outpu	t	Function
SHCP	STCP	OE	MR	DS	Q7S	Qn	
Χ	Χ	L	L	X	L	NC	a LOW-level on MR only affects the shift registers
Χ	↑	L	L	X	L	L	empty shift register loaded into storage register
Χ	Χ	Н	L	Χ	L	Z	shift register clear; parallel outputs in high-impedance OFF-state
↑	X	L	Н	Н	Q6S	NC	logic HIGH-level shifted into shift register stage 0. Contents of all shift register stages shifted through, e.g. previous state of stage 6 (internal Q6S) appears on the serial output (Q7S).
X	↑	L	Н	Χ	NC	QnS	contents of shift register stages (internal QnS) are transferred to the storage register and parallel output stages
↑	↑	L	Н	X	Q6S	QnS	contents of shift register shifted through; previous contents of the shift register is transferred to the storage register and the parallel output stages

[1] H = HIGH voltage state;

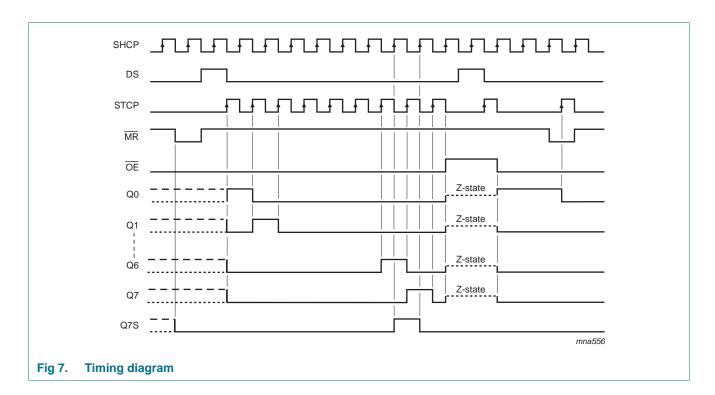
L = LOW voltage state;

↑ = LOW-to-HIGH transition;

X = don't care;

NC = no change;

Z = high-impedance OFF-state.



8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
V_{I}	input voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_{I} < -0.5 \text{ V}$	<u>[1]</u> –20	-	mA
I _{OK}	output clamping current	V_O < -0.5 V or V_O > V_{CC} + 0.5 V	<u>[1]</u> –20	+20	mA
Io	output current	$V_{O} = -0.5 \text{ V to } (V_{CC} + 0.5 \text{ V})$	-25	+25	mA
I _{CC}	supply current		-	+75	mA
I_{GND}	ground current		−75	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2] -	500	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 5. Operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
74VHC595-	Q100					
V_{CC}	supply voltage		2.0	5.0	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage		0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	100	ns/V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	20	ns/V
74VHCT59	5-Q100					
V _{CC}	supply voltage		4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	20	ns/V

^[2] For SO16 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K.
For TSSOP16 packages: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K.
For DHVQFN16 packages: above 60 °C the value of P_{tot} derates linearly at 4.5 mW/K.

10. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C	;	-40 °C	to +85 °C	-40 °C	to +125 °C	Uni
			Min	Тур	Max	Min	Max	Min	Max	
74VHC5	95-Q100	'	·		,					
V_{IH}	HIGH-level	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
	input voltage	V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V _{IL}	LOW-level	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
	input voltage	V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V_{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_{O} = -50 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -50 \mu A; V_{CC} = 3.0 V$	2.9	3.0	-	2.9	-	2.9	-	V
		$I_{O} = -50 \mu A$; $V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		$I_{O} = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.80	-	3.70	-	V
V _{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = 50 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 3.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
		$I_O = 8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
l _l	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	-	0.1	-	1.0	-	2.0	μΑ
l _{oz}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.25	-	±2.5	-	±10	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	4.0	-	40	-	80	μА
Cı	input capacitance		-	3	10	-	10	-	10	pF
74VHCT	595-Q100									
V _{IH}	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	-	-	2.0	-	2.0	-	٧
V _{IL}	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
011	output voltage	$I_{O} = -50 \mu\text{A}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -8.0 \text{ mA}$	3.94	-	-	3.80	-	3.70	-	V
V _{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
OL.	output voltage	$I_{O} = 50 \mu\text{A}$	-	0	0.1	-	0.1	-	0.1	V
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 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C	;	–40 °C t	o +85 °C	–40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
l _l	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μΑ
I _{OZ}	OFF-state output current	$\begin{split} &V_{I}=V_{IH} \text{ or } V_{IL};\\ &V_{O}=V_{CC} \text{ or GND per input pin;}\\ &\text{other inputs at } V_{CC} \text{ or GND;}\\ &I_{O}=0 \text{ A; } V_{CC}=5.5 \text{ V} \end{split}$	-	-	±0.25	-	±2.5	-	±10	μА
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	4.0	-	40	-	80	μΑ
ΔI_{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}$; other inputs at V_{CC} or GND; $I_O = 0 \text{ A}$; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
Cı	input capacitance		-	3	10	-	10	-	10	pF

11. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 13.

Symbol	Parameter	Conditions			25 °C		-40 °C t	o +85 °C	-40 °C 1	to +125 °C	Unit
			ı	Min	Typ[1]	Max	Min	Max	Min	Max	
74VHC5	95-Q100				•		'		'		•
t _{pd}	propagation	SHCP to Q7S; see Figure 8	[2]								
	delay	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$									
		$C_L = 15 pF$		-	5.7	13.0	1.0	15.0	1.0	16.5	ns
		$C_L = 50 pF$		-	7.7	16.5	1.0	18.5	1.0	20.1	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$									
		$C_L = 15 pF$		-	4.0	8.2	1.0	9.4	1.0	10.5	ns
		$C_L = 50 pF$		-	5.4	10.0	1.0	11.4	1.0	12.5	ns
		STCP to Qn; see Figure 9	[2]								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$									
		$C_L = 15 pF$		-	5.9	11.9	1.0	13.5	1.0	15.0	ns
		$C_L = 50 pF$		-	7.7	15.4	1.0	17.0	1.0	18.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$									
		C _L = 15 pF		-	4.2	7.4	1.0	8.5	1.0	9.5	ns
		$C_L = 50 pF$		-	5.5	9.0	1.0	10.5	1.0	11.5	ns
		MR to Q7S; see Figure 11	[3]								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$									
		C _L = 15 pF		-	5.9	12.8	1.0	13.7	1.0	15.0	ns
		$C_L = 50 pF$		-	7.4	16.3	1.0	17.2	1.0	18.7	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$									
		C _L = 15 pF		-	4.4	8.0	1.0	9.1	1.0	10.0	ns
		C _L = 50 pF		-	5.6	10.0	1.0	11.1	1.0	12.0	ns

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 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 13.

Symbol	Parameter	Conditions		25 °C		-40 °C	to +85 °C	-40 °C t	o +125 °C	Unit
			Min	Typ[1]	Max	Min	Max	Min	Max	
t _{en}	enable time	OE to Qn; see Figure 12	<u>4]</u>		•	'				
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$								
		C _L = 15 pF	-	5.6	11.5	1.0	13.5	1.0	15.0	ns
		$C_L = 50 \text{ pF}$	-	7.4	15.0	1.0	17.0	1.0	18.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$								
		C _L = 15 pF	-	4.0	8.6	1.0	10.0	1.0	11.0	ns
		C _L = 50 pF	-	5.3	10.6	1.0	12.0	1.0	13.0	ns
t _{dis}	disable time	OE to Qn; see Figure 12	<u>5]</u>							
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$								
		C _L = 15 pF	-	5.4	11.0	1.0	13.0	1.0	14.5	ns
		C _L = 50 pF	-	8.7	15.7	1.0	16.2	1.0	17.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$								
		$C_L = 15 pF$	-	3.8	8.0	1.0	9.5	1.0	10.5	ns
		$C_L = 50 pF$	-	5.8	10.3	1.0	11.0	1.0	12.0	ns
f _{max}	maximum frequency	SHCP or STCP; see Figure 8 and 9								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	80	125	-	60	-	40	-	MHz
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	130	170	-	110	-	90	-	MHz
t _W	pulse width	SHCP HIGH or LOW; see Figure 8								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	5.0	-	-	5.0	-	5.0	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	5.0	-	-	5.0	-	5.0	-	ns
		STCP HIGH or LOW; see Figure 9								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	5.0	-	-	5.0	-	5.0	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	5.0	-	-	5.0	-	5.0	-	ns
		MR LOW; see Figure 11								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	5.0	-	-	5.0	-	5.0	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	5.0	-	-	5.0	-	5.0	-	ns
t _{su}	set-up time	DS to SHCP; see Figure 9								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	3.5	-	-	3.5	-	3.5	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	3.0	-	-	3.0	-	3.0	-	ns
		SHCP to STCP; see Figure 10								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	8.5	-	-	8.5	-	8.5	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	5.0	-	-	5.0	-	5.0	-	ns
t _h	hold time	DS to SHCP; see Figure 10								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.5	-	-	1.5	-	1.5	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	-	-	2.0	-	2.0	-	ns

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 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 13.

Symbol	Parameter	Conditions			25 °C		-40 °C	to +85 °C	–40 °C t	o +125 °C	Unit
				Min	Typ[1]	Max	Min	Max	Min	Max	
t_{rec}	recovery	MR to SHCP; see Figure 11									
	time	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		3.0	-	-	3.0	-	3.0	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		2.5	-	-	2.5	-	2.5	-	ns
C_{PD}	power dissipation capacitance	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$	[6] [7]	-	180	-	-	-	-	-	pF
74VHCT	595-Q100; V _C	_{CC} = 4.5 V to 5.5 V									
t _{pd}		SHCP to Q7S; see Figure 8	[2]								
	delay	C _L = 15 pF		-	3.8	8.2	1.0	9.0	1.0	10.0	ns
		$C_L = 50 pF$		-	5.2	10.0	1.0	11.0	1.0	12.0	ns
		STCP to Qn; see Figure 9	[2]								
		$C_L = 15 pF$		-	4.0	7.4	1.0	8.5	1.0	9.5	ns
		$C_L = 50 pF$		-	5.3	9.0	1.0	10.5	1.0	11.5	ns
		MR to Q7S; see Figure 11	[3]								
		$C_L = 15 pF$		-	4.6	8.2	1.0	9.5	1.0	10.5	ns
		$C_L = 50 pF$		-	5.8	10.5	1.0	11.5	1.0	12.5	ns
t_{en}	enable time	OE to Qn; see Figure 12	<u>[4]</u>								
		C _L = 15 pF		-	4.8	9.0	1.0	11.0	1.0	12.0	ns
		C _L = 50 pF		-	6.2	11.6	1.0	13.0	1.0	14.5	ns
t_{dis}	disable time	OE to Qn; see Figure 12	<u>[5]</u>								
		C _L = 15 pF		-	3.6	6.9	1.0	8.0	1.0	9.0	ns
		$C_L = 50 pF$		-	5.8	10.3	1.0	11.0	1.0	12.0	ns
f _{max}	maximum frequency	SHCP and STCP; see Figure 8 and 9		130	170	-	110	-	90	-	MHz
t_{W}	pulse width	SHCP HIGH or LOW; see Figure 8		5.0	-	-	5.0	-	5.0	-	ns
		STCP HIGH or LOW; see Figure 9		5.0	-	-	5.0	-	5.0	-	ns
		MR LOW; see Figure 11		5.0	-	-	5.0	-	5.0	-	ns
t _{su}	set-up time	DS to SHCP; see Figure 9		3.0	-	-	3.0	-	3.0	-	ns
		SHCP to STCP; see Figure 10		5.0	-	-	5.0	-	5.0	-	ns
t _h	hold time	DS to SHCP; see Figure 10		2.0	-	-	2.0	-	2.0	-	ns
t _{rec}	recovery time	MR to SHCP; see Figure 11		3.0	-	-	3.0	-	3.0	-	ns

Table 7. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 13.

Symbol	Parameter	Conditions		25 °C			-40 °C 1	o +85 °C	-40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	Min	Max	
C_{PD}	power dissipation capacitance	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$	[6] [7]	-	190	-	-	-	-	-	pF

- [1] Typical values are measured at nominal supply voltage.
- [2] t_{pd} is the same as t_{PHL} and t_{PLH} .
- [3] t_{pd} is the same as t_{PHL} only.
- [4] t_{en} is the same as t_{PZL} and t_{PZH} .
- [5] t_{dis} is the same as t_{PLZ} and t_{PHZ} .
- [6] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma (C_L \times V_{CC}^2 \times f_o)$$
 where:

f_i = input frequency in MHz;

 f_0 = output frequency in MHz;

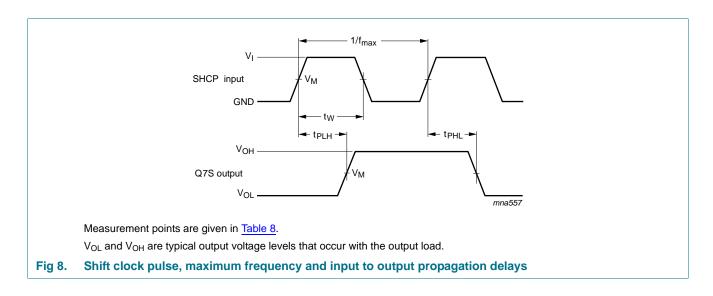
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs;

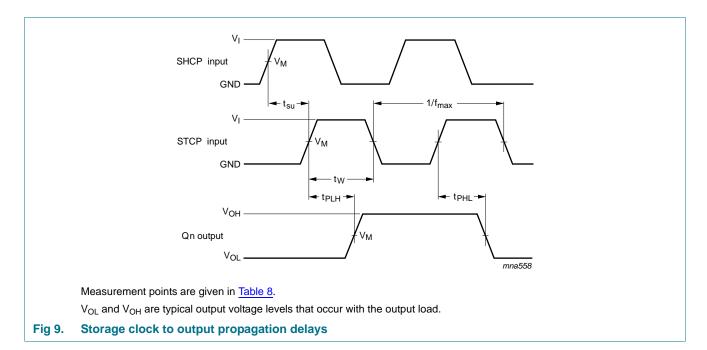
C_L = output load capacitance in pF;

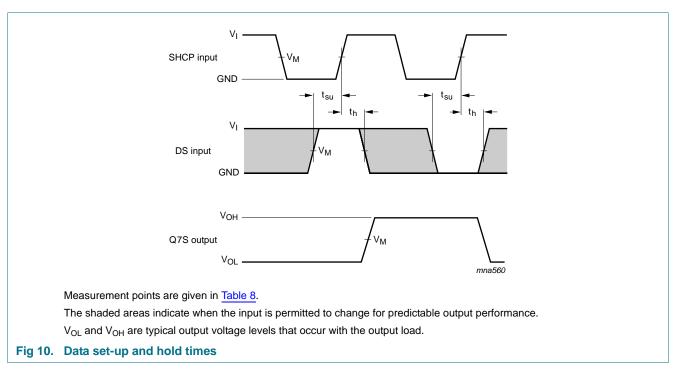
 V_{CC} = supply voltage in V.

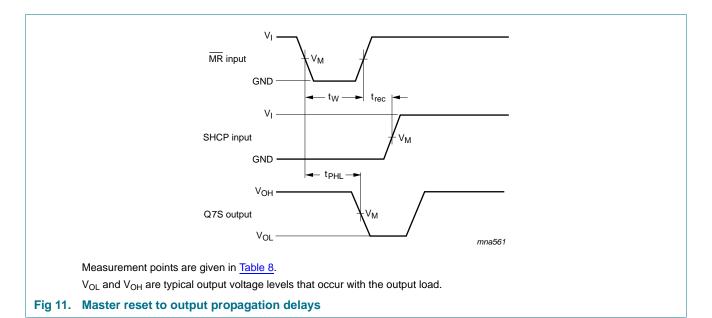
[7] All 9 outputs switching.

12. Waveforms









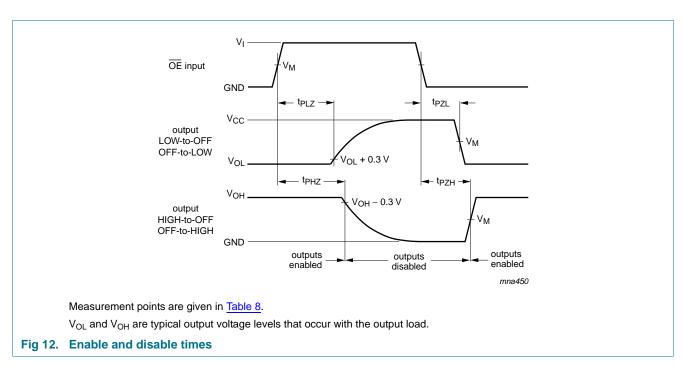
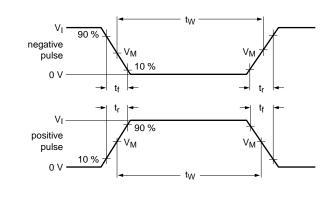
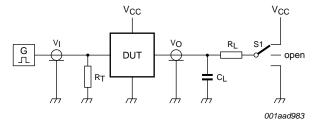


Table 8. Measurement points

Туре	Input	Output
	V _M	V _M
74VHC595-Q100	0.5V _{CC}	0.5V _{CC}
74VHCT595-Q100	1.5 V	0.5V _{CC}





Test data is given in Table 9.

Definitions for test circuit:

 C_L = load capacitance including jig and probe capacitance.

 R_L = load resistance.

 R_T = termination resistance should be equal to the output impedance Z_0 of the pulse generator.

S1 = test selection switch.

Fig 13. Load circuitry for switching times

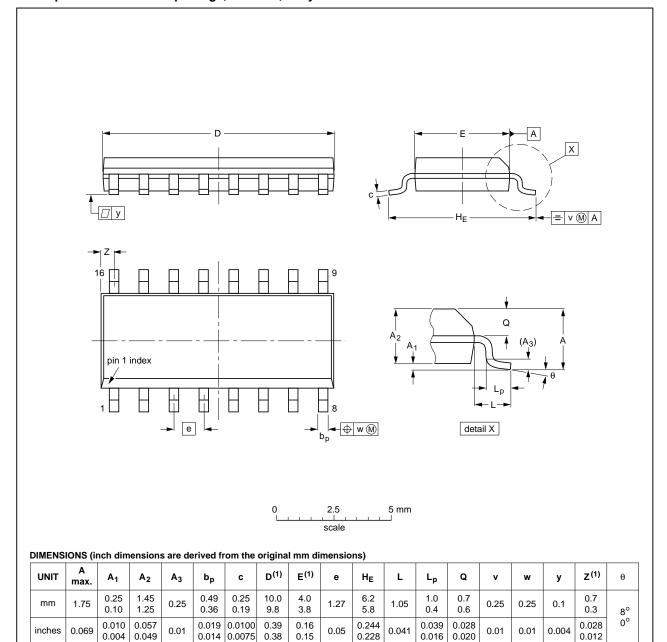
Table 9. Test data

Туре	Input		Load		S1 position			
	VI	t _r , t _f	CL	R_L	t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}	
74VHC595-Q100	V_{CC}	\leq 3.0 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}	
74VHCT595-Q100	3.0 V	\leq 3.0 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}	

13. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT109-1	076E07	MS-012			99-12-27 03-02-19	

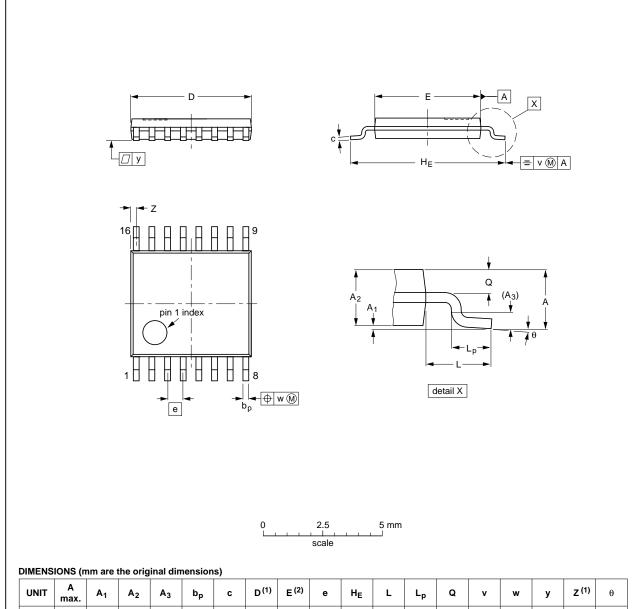
Fig 14. Package outline SOT109-1 (SO16)

74VHC_VHCT595_Q100

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TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT403-1		MO-153				-99-12-27 03-02-18	

Fig 15. Package outline SOT403-1 (TSSOP16)

74VHC_VHCT595_Q100

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DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm SOT763-1

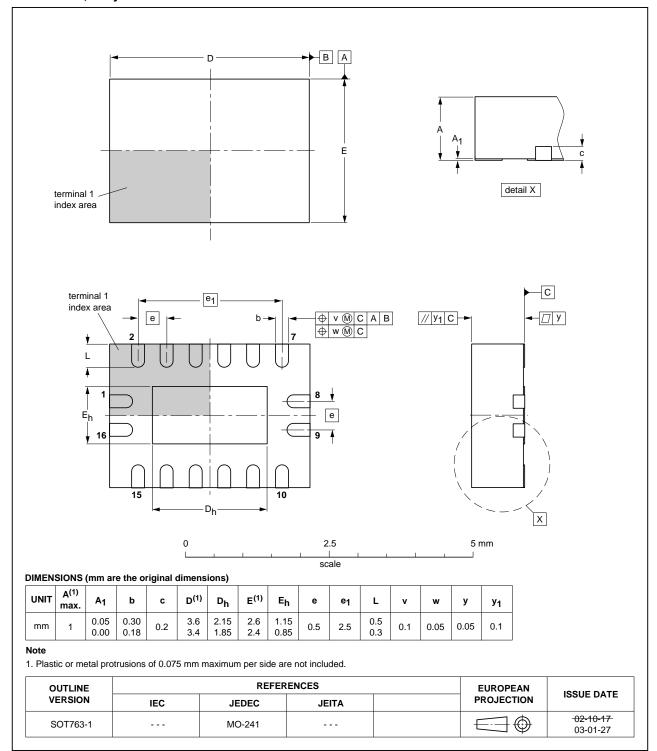


Fig 16. Package outline SOT763-1 (DHVQFN16)

74VHC_VHCT595_Q100

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14. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MIL	Military
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74VHC_VHCT595_Q100 v.1	20131115	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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74VHC_VHCT595_Q100

74VHC595-Q100; 74VHCT595-Q100

8-bit serial-in/serial-out or parallel-out shift register with output latches

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